

YJ Planar Schottky Barrier Diode Die Specification

100V 5A, 65mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB065H100SS-280A

Main Products Characterstics

Maximum Ratings	Static Electrical Characteristics (Ta = 25°C)	
	Spec	Value
	105 V	120V
Maximum forward voltage drop		
I _F = 5 A	0.82V	0.77V
	≤ 2%	
	5uA	0.3uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	60.6 Mils
Active Area	57 Mils
Top Metal	
Back Metal	
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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